

# One Watt High Current Transistors

## **NPN Silicon**

## MPSW01 MPSW01A\*

\*ON Semiconductor Preferred Device

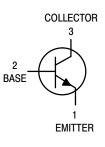
### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit		
Collector–Emitter Voltage MPSW01 MPSW01A	V <sub>CEO</sub>	30 40	Vdc		
Collector-Base Voltage MPSW01 MPSW01A	V <sub>CBO</sub>	40 50	Vdc		
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc		
Collector Current — Continuous	Ic	1000	mAdc		
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.0 8.0	Watts mW/°C		
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.5 20	Watts mW/°C		
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C		



#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	50	°C/W



## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	MPSW01 MPSW01A	V <sub>(BR)CEO</sub>	30 40		Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 100 μAdc, I <sub>E</sub> = 0)	MPSW01 MPSW01A	V <sub>(BR)CBO</sub>	40 50		Vdc
Emitter–Base Breakdown Voltage $(I_E = 100 \mu Adc, I_C = 0)$		V <sub>(BR)EBO</sub>	5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 40 \text{ Vdc}, I_E = 0)$	MPSW01 MPSW01A	I <sub>CBO</sub>		0.1 0.1	μAdc
Emitter Cutoff Current $(V_{EB} = 3.0 \text{ Vdc}, I_C = 0)$		I <sub>EBO</sub>	_	0.1	μAdc

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

### MPSW01 MPSW01A

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS <sup>(1)</sup>	•	•	•	•
DC Current Gain $ \begin{aligned} &(I_C=10 \text{ mAdc}, V_{CE}=1.0 \text{ Vdc}) \\ &(I_C=100 \text{ mAdc}, V_{CE}=1.0 \text{ Vdc}) \\ &(I_C=1000 \text{ mAdc}, V_{CE}=1.0 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	55 60 50	_ _ _	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 1000 mAdc, I <sub>B</sub> = 100 mAdc)	V <sub>CE</sub> (sat)	_	0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 1000 mAdc, V <sub>CE</sub> = 1.0 Vdc)	V <sub>BE(on)</sub>	_	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u>,                                      </u>			•
Current-Gain — Bandwidth Product (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 10 Vdc, f = 20 MHz)	f <sub>T</sub>	50	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	_	20	pF

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

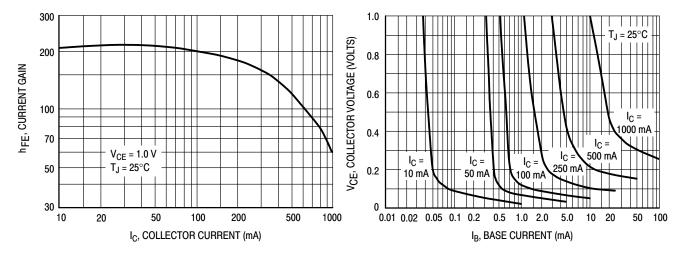


Figure 1. DC Current Gain

Figure 2. Collector Saturation Region

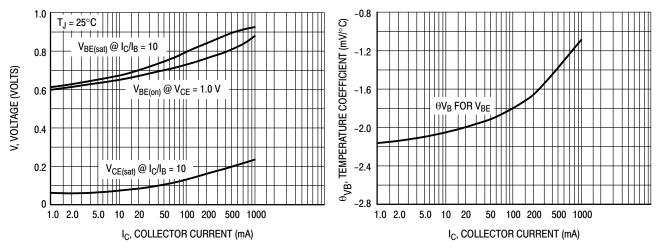


Figure 3. "ON" Voltages

**Figure 4. Temperature Coefficient** 

## MPSW01 MPSW01A

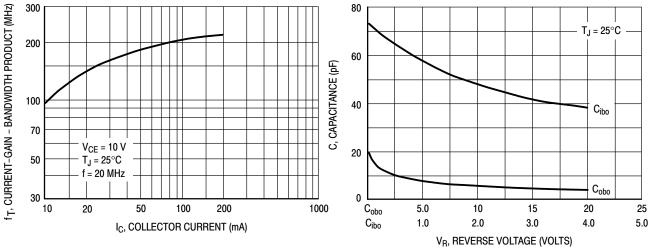


Figure 5. Current Gain — Bandwidth Product

Figure 6. Capacitance

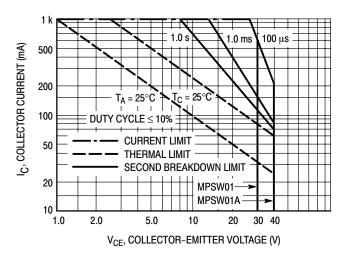
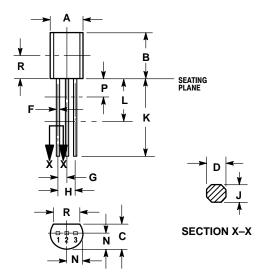


Figure 7. Active Region — Safe Operating Area

#### MPSW01 MPSW01A

## PACKAGE DIMENSIONS

TO-92 (TO-226) **CASE 29-10 ISSUE AL** 



1F 5 PIN 1. DRAIN

SOURCE

GATE

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

  DIMENSION F APPLIES BETWEEN P AND L.
- DIMENSIONS D AND J APPLY BETWEEN L AND K
  MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	METERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.44	5.21	
В	0.290	0.310	7.37	7.87	
С	0.125	0.165	3.18	4.19	
D	0.018	0.021	0.457	0.533	
F	0.016	0.019	0.407	0.482	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.018	0.024	0.46	0.61	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.135		3.43		

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